ABSTRACT OF THE DISCLOSURE

A semiconductor device manufacturing method comprises a step of forming a laminated structure by adhering, on a semiconductor substrate including a plurality of integrated circuits, a carrier member covering a region in which the plurality of integrated circuits are formed, with an insulating resin interposed between the semiconductor substrate and the carrier member, a step of cutting a notch into the laminated structure so as to cut the semiconductor substrate together with the insulating resin while allowing at least a portion of the carrier member to remain uncut, and a dicing step for dividing the laminated structure by cutting the carrier member. The notch cutting step is performed while cooling a dicing saw used to cut the semiconductor substrate.